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Kind regards,

Team Nexperia



Low capacitance bidirectional ESD protection diodes in SOD323

Rev. 02 — 20 August 2009

Product data sheet

1. Product profile

1.1 General description

Bidirectional ElectroStatic Discharge (ESD) protection diodes in a very small SOD323 (SC-76) SMD plastic package designed to protect one signal line from the damage caused by ESD and other transients.

1.2 Features

- Bidirectional ESD protection of one line ESD protection > 23 kV
- Max. peak pulse power: P_{pp} = 500 W IEC 61000-4-2, level 4 (ESD)
- Low clamping voltage: $V_{(CL)R} = 26 \text{ V}$ IEC 61000-4-5 (surge); $I_{pp} = 18 \text{ A}$
- Ultra low leakage current: I_{RM} < 0.09 µA Very small SMD plastic package

1.3 Applications

- Computers and peripherals
- Communication systems
- Audio and video equipment
- Data lines
- CAN bus protection

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RWM}	reverse stand-off voltage					
	PESD3V3L1BA		-	-	3.3	V
	PESD5V0L1BA		-	-	5.0	V
	PESD12VL1BA		-	-	12	V
	PESD15VL1BA		-	-	15	V
	PESD24VL1BA		-	-	24	V
C _d	diode capacitance	$V_R = 0 V;$ f = 1 MHz				
	PESD3V3L1BA		-	101	-	pF
	PESD5V0L1BA		-	75	-	pF
	PESD12VL1BA		-	19	-	pF
	PESD15VL1BA		-	16	-	pF
	PESD24VL1BA		-	11	-	pF



Low capacitance bidirectional ESD protection diodes in SOD323

Pinning information 2.

Table 2. Pinning

	9		
Pin	Description	Simplified outline	Symbol
1	cathode 1		
2	cathode 2	1 2	1 2 sym045

Ordering information 3.

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
PESDxL1BA series	SC-76	plastic surface mounted package; 2 leads	SOD323

Marking

Table 4. **Marking codes**

Type number	Marking code
PESD3V3L1BA	AB
PESD5V0L1BA	AC
PESD12VL1BA	AD
PESD15VL1BA	AE
PESD24VL1BA	AF

PESDXL1BA_SER_2 Rev. 02 — 20 August 2009

Product data sheet

2 of 15

Low capacitance bidirectional ESD protection diodes in SOD323

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	•		
Symbol	Parameter	Conditions	Min	Max	Unit
P_{pp}	peak pulse power	8/20 μs	<u>[1]</u>		
	PESD3V3L1BA		-	500	W
	PESD5V0L1BA		-	500	W
	PESD12VL1BA		-	200	W
	PESD15VL1BA		-	200	W
	PESD24VL1BA		-	200	W
I_{pp}	peak pulse current	8/20 μs	<u>[1]</u>		
	PESD3V3L1BA		-	18	Α
	PESD5V0L1BA		-	15	Α
	PESD12VL1BA		-	5	Α
	PESD15VL1BA		-	5	Α
	PESD24VL1BA		-	3	Α
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Non-repetitive current pulse 8/20 μ s exponential decay waveform; see Figure 1.

Table 6. ESD maximum ratings

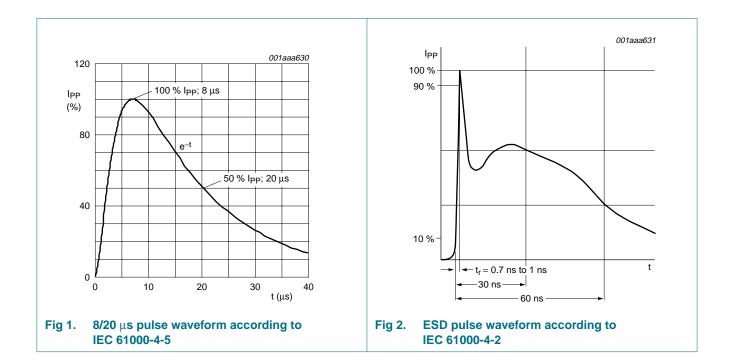
Symbol	Parameter	Conditions	Min	Max	Unit
ESD	electrostatic discharge capability	IEC 61000-4-2 (contact discharge)	[1]		
	PESD3V3L1BA		-	30	kV
	PESD5V0L1BA		-	30	kV
	PESD12VL1BA		-	30	kV
	PESD15VL1BA		-	30	kV
	PESD24VL1BA		-	23	kV
	PESDxL1BA series	HBM MIL-Std 883	-	10	kV

^[1] Device stressed with ten non-repetitive ESD pulses; see Figure 2.

Table 7. ESD standards compliance

Standard	Conditions
IEC 61000-4-2; level 4 (ESD); Figure 2	> 15 kV (air); > 8 kV (contact)
HBM MIL-Std 883; class 3	> 4 kV

Low capacitance bidirectional ESD protection diodes in SOD323



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Product data sheet

4 of 15

Low capacitance bidirectional ESD protection diodes in SOD323

6. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RWM}	reverse stand-off voltage					
	PESD3V3L1BA		-	-	3.3	V
	PESD5V0L1BA		-	-	5.0	V
	PESD12VL1BA		-	-	12	V
	PESD15VL1BA		-	-	15	V
	PESD24VL1BA		-	-	24	V
I _{RM}	reverse leakage current	see Figure 7				
	PESD3V3L1BA	$V_{RWM} = 3.3 V$	-	0.09	2	μΑ
	PESD5V0L1BA	$V_{RWM} = 5.0 V$	-	0.01	1	μΑ
	PESD12VL1BA	$V_{RWM} = 12 V$	-	< 1	50	nA
	PESD15VL1BA	$V_{RWM} = 15 V$	-	< 1	50	nA
	PESD24VL1BA	$V_{RWM} = 24 V$	-	< 1	50	nA
$V_{(BR)}$	breakdown voltage	$I_R = 5 \text{ mA}$				
	PESD3V3L1BA		5.8	6.4	6.9	V
	PESD5V0L1BA		7.0	7.6	8.2	V
	PESD12VL1BA		14.2	15.9	16.7	V
	PESD15VL1BA		17.1	18.9	20.3	V
	PESD24VL1BA		25.4	27.8	30.3	V
C _d	diode capacitance	V _R = 0 V; f = 1 MHz; see <u>Figure 5</u> and <u>6</u>				
	PESD3V3L1BA		-	101	-	pF
	PESD5V0L1BA		-	75	-	pF
	PESD12VL1BA		-	19	-	pF
	PESD15VL1BA		-	16	-	pF
	PESD24VL1BA		-	11	-	pF
V _{(CL)R}	clamping voltage		<u>[1]</u>			
	PESD3V3L1BA	I _{pp} = 1 A	-	-	8	V
		I _{pp} = 18 A	-	-	26	V
	PESD5V0L1BA	I _{pp} = 1 A	-	-	10	V
		I _{pp} = 15 A	-	-	33	V
	PESD12VL1BA	I _{pp} = 1 A	-	-	20	V
		$I_{pp} = 5A$	-	-	37	V
	PESD15VL1BA	I _{pp} = 1 A	-	-	25	V
		I _{pp} = 5 A	-	-	44	V
	PESD24VL1BA	I _{pp} = 1 A	-	-	40	V
		$I_{pp} = 3 A$	-	-	70	V

Low capacitance bidirectional ESD protection diodes in SOD323

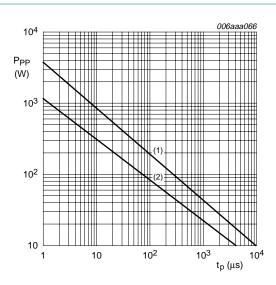
 Table 8.
 Characteristics ...continued

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
r_{dif}	differential resistance	$I_R = 1 \text{ mA}$				
	PESD3V3L1BA		-	-	400	Ω
	PESD5V0L1BA		-	-	80	Ω
	PESD12VL1BA		-	-	200	Ω
	PESD15VL1BA		-	-	225	Ω
	PESD24VL1BA		-	-	300	Ω

^[1] Non-repetitive current pulse 8/20 μ s exponential decay waveform; see Figure 1.

Low capacitance bidirectional ESD protection diodes in SOD323



 $T_{amb} = 25 \, ^{\circ}C$

 t_p = 8/20 μ s exponential decay waveform; see Figure 1

- (1) PESD3V3L1BA and PESD5V0L1BA
- (2) PESD12VL1BA; PESD15VL1BA; PESD24VL1BA

Fig 3. Peak pulse power dissipation as a function of pulse time; typical values

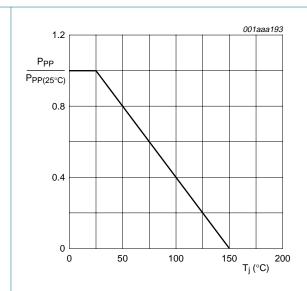
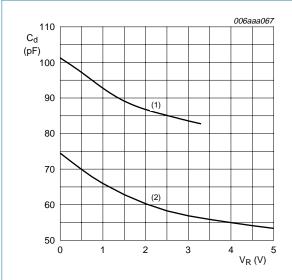


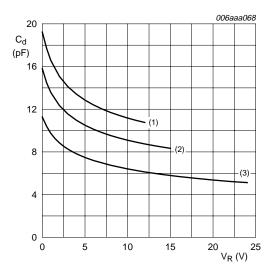
Fig 4. Relative variation of peak pulse power as a function of junction temperature; typical values



 T_{amb} = 25 °C; f = 1 MHz

- (1) PESD3V3L1BA
- (2) PESD5V0L1BA

Fig 5. Diode capacitance as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$

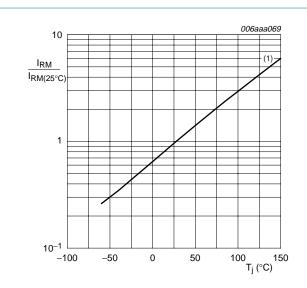
- (1) PESD12VL1BA
- (2) PESD15VL1BA
- (3) PESD24VL1BA

Fig 6. Diode capacitance as a function of reverse voltage; typical values

7 of 15

8 of 15

Low capacitance bidirectional ESD protection diodes in SOD323

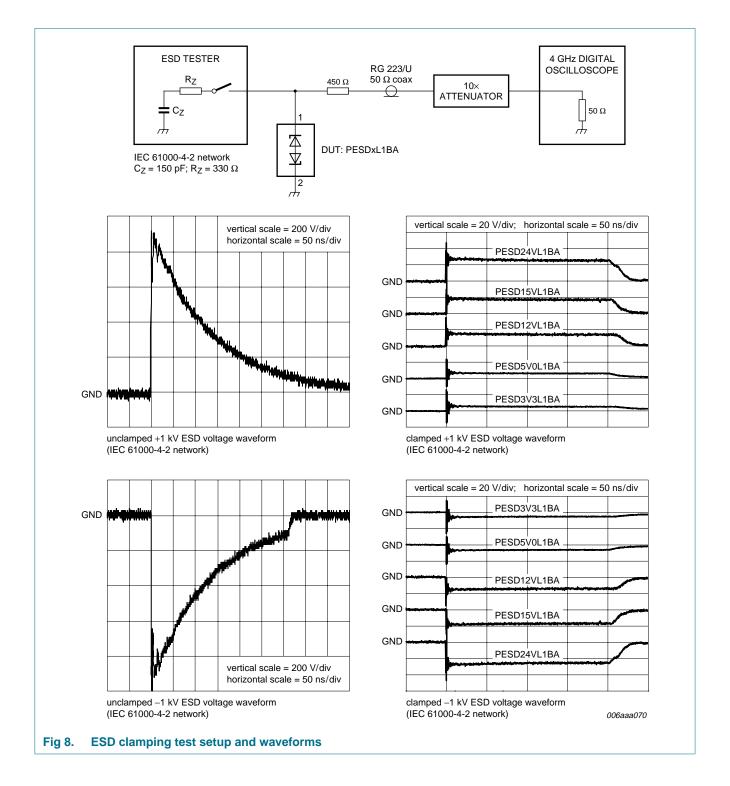


(1) PESD3V3L1BA; PESD5V0L1BA For PESD12VL1BA, PESD15VL1BA and PESD24VL1BA, I_{RM} < 20 nA at 150 $^{\circ}\text{C}$

Relative variation of reverse leakage current as a function of junction temperature; typical values Fig 7.

Product data sheet

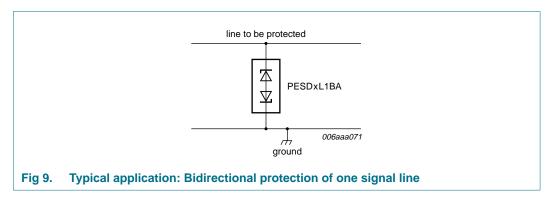
Low capacitance bidirectional ESD protection diodes in SOD323



Low capacitance bidirectional ESD protection diodes in SOD323

7. Application information

The PESDxL1BA series is designed for bidirectional protection of one signal line from the damage caused by ElectroStatic Discharge (ESD) and surge pulses. The PESDxL1BA series may be used on lines where the signal polarity is above and below ground. The PESDxL1BA series provides a surge capability of up to 500 W per line for a 8/20 μ s waveform.



Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the protection device as close to the input terminal or connector as possible.
- 2. The path length between the protection device and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductor.
- 5. Minimize all printed-circuit board conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer printed-circuit boards, use ground vias.

Low capacitance bidirectional ESD protection diodes in SOD323

Package outline

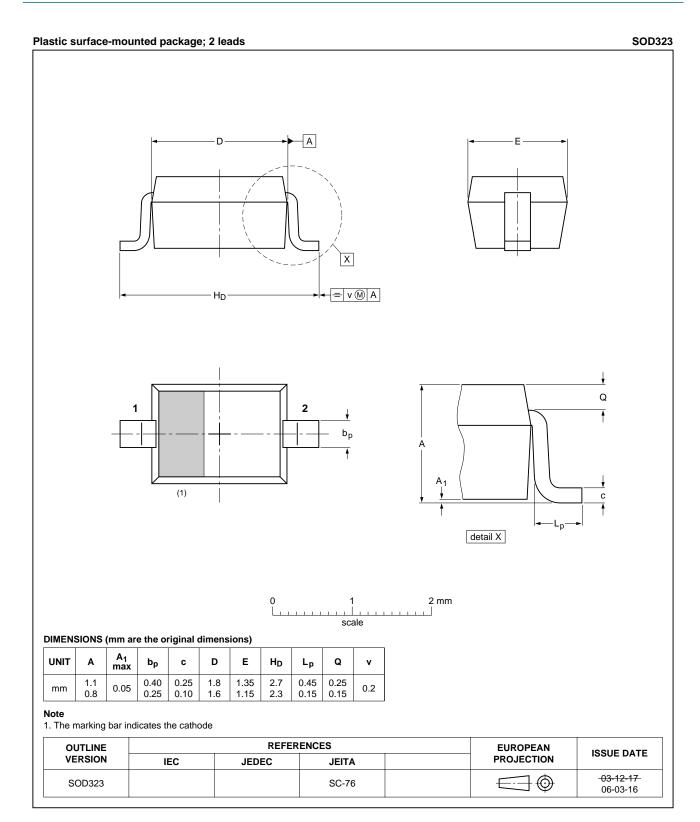


Fig 10. Package outline SOD323 (SC-76)

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Product data sheet

Low capacitance bidirectional ESD protection diodes in SOD323

9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	escription Packing quantity	
			3000	10000
PESDxL1BA series	SOD323	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 12.

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Product data sheet Rev. 02 — 20 August 2009 12 of 15

Low capacitance bidirectional ESD protection diodes in SOD323

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESDXL1BA_SER_2	20090820	Product data sheet	-	PESDXL1BA_SER_1
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 10 "Package outline SOD323 (SC-76)": updated 			
PESDXL1BA_SER_1	20041004	Product data sheet	-	-

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Product data sheet

Low capacitance bidirectional ESD protection diodes in SOD323

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Low capacitance bidirectional ESD protection diodes in SOD323

13. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information
4	Marking 2
5	Limiting values 3
6	Characteristics 5
7	Application information 10
8	Package outline
9	Packing information 12
10	Revision history
11	Legal information
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks14
12	Contact information
13	Contents

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